

REMARKS

Reconsideration and allowance of the above-referenced application are respectfully submitted.

Claims 8, 9, and 10 stand rejected under 35 U.S.C. 102(e) as allegedly being anticipated by Wakai, U.S. Patent No. 5,821,137. Claim 11 stands rejected over Wakai in view of Katayama.

The rejection contends that Wakai discloses a pair of portions containing n-type and p-type impurities in its FIG. 4E. The rejection contends that these impurities are formed adjacent to source and drain regions. For purposes of answering this, we will assume that the Examiner intends the p^- -denoted regions as being source and drain regions, and the n^+ regions being a pair of portions with n-type and p-type impurities. In FIG. 4, however, the p^- -regions appear to be LDD regions. The n^+ regions appear to be source and drain regions. Therefore, it is respectfully suggested that this interpretation does not hold properly true. For these reasons, it is respectfully suggested that the 103(e) rejection based on Wakai is incorrect, and likewise, that the 103 rejection based on Wakai is also incorrect. As such, it is respectfully suggested that the rejection does not meet the Patent Office's burden of providing a *prima facie* showing of unpatentability and, therefore, that all of these claims should be in condition for allowance.

Claim 8 stands rejected under 35 U.S.C. 11, second paragraph, and in response, the term "second" has been deleted.

Claims 1-11 stand rejected based on judicially created obviousness-type double patenting over U.S. Patent No. 6,194,762. However, it is respectfully suggested that the '762 patent does not teach that an electrode is connected to at least one of the pair of portions containing n-type and p-type electrodes. Moreover, this connection is not well known, and specifically it is not well known that an electrode should be connected to a pair of portions adjacent to source and drain regions. For these reasons, it is respectfully suggested that the obviousness-type double patenting is in error and should be withdrawn.

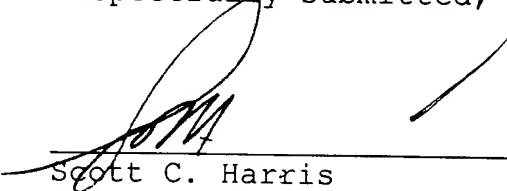
In view of the above amendments and remarks, therefore, all of the claims should be in condition for allowance. A formal notice to that effect is respectfully solicited.

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Respectfully submitted,

Date: _____

6/27/02



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VERSION TO SHOW CHANGES MADE

In the Claims:

Please amend claim 8 as follows.

8. (Amended) A semiconductor device having at least one thin film transistor formed over a substrate, said thin film transistor comprising:

a semiconductor layer having a source and drain regions and a channel forming region therebetween;

a gate electrode adjacent to said channel forming region with a gate insulating layer interposed therebetween,

wherein said channel forming region directly contacts with said [second] source and drain regions,

wherein a pair of portions containing n-type and p-type impurities are formed adjacent to said source and drain region, and

wherein an electrode is connected to at least one of said pair of portions.